

AMENDMENTS TO THE SPECIFICATION

Please amend the specification as follows:

Amend the paragraph beginning on page 17, line 25 as follows:

Next, an entire surface is coated with ~~pheteresit~~ photoresist, and patterning of the photoresist is performed with the photolithography technique, whereby a resist mask 31 which is provided with an opening in each of regions in which the PMOS transistors (the PMOS normal transistor and the PMOS high voltage transistor) are to be formed is formed, as shown in Fig. 6A to Fig. 6D. Next, ion implantation of N-type impurities is performed with the resist mask 31 as a mask, whereby N wells 9 are formed. Then, the resist mask 31 is removed.